

1N4150

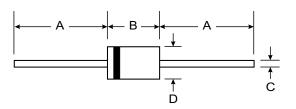
FAST SWITCHING DIODE

Features

- Ideal for Fast Logic Applications
- Ultra Fast Switching
- High Reliability
- High Conductance

Mechanical Data

- Case: DO-35, Plastic
- Leads: Solderable per MIL-STD-202, Method 208
- Marking: Type Number
- Polarity: Cathode Band
- Weight: 0.13 grams (approx.)



DO-35					
Dim	Min	Мах			
Α	25.40	—			
В	_	4.00			
С	_	0.60			
D		2.00			
All Dimensions in mm					

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	1N4150	Unit
Non-Repetitive Peak Reverse Voltage @ 5.0µA	V _{RM}	V _{RM} 75	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	V
RMS Reverse Voltage	V _{R(RMS)}	35	V
Forward Continuous Current (Note 1)	I _{FM}	400	mA
Average Rectified Output Current (Note 1)	IO	200	mA
Repetitive Peak Forward Current (Note 1)	I _{FRM}	600	mA
Non-Repetitive Peak Forward Surge Current $@ t \le 1.0s$ @ t = 1.0µs	IFSM	1.0 4.0	А
Power Dissipation (Note 1)	Pd	500	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	300	K/W
Operating and Storage Temperature Range	Tj, T _{STG}	-65 to +200	٥C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage Drop	V _{FM}	0.54 0.66 0.76 0.82 0.87	0.62 0.74 0.86 0.92 1.0	V	
Maximum Peak Reverse Current	I _{RM}		100	nA μA	$\begin{array}{l} T_A = ~25^\circ C \\ T_A = ~150^\circ C \end{array}$
Junction Capacitance	Cj		2.5	pF	V _R = 0V, f = 1.0MHz
Reverse Recovery Time	t _{rr}		4.0	ns	$ I_F = I_R = 200 \text{mA}, \\ I_{rr} = 0.1 \text{ x } I_R, R_L = 100 \Omega $
Forward Recovery Time	t _{fr}	_	10	ns	I _F = 200mA, V _{FR} = 1.0V

Note: 1. Valid provided that leads are kept at ambient temperature.